



SOT-23 Plastic-Encapsulate Transistors

S8050D TRANSISTOR (NPN)

FEATURES

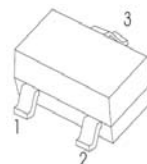
- High Collector Current.
- Complementary to S8550D
- Excellent h_{FE} Linearity.

MARKING: J3Y

MAXIMUM RATINGS ($T_a=25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Value	Unit
V_{CBO}	Collector-Base Voltage	40	V
V_{CEO}	Collector-Emitter Voltage	25	V
V_{EBO}	Emitter-Base Voltage	5	V
I_C	Collector Current	800	mA
P_C	Collector Power Dissipation	300	mW
$R_{\theta JA}$	Thermal Resistance From Junction To Ambient	416	$^\circ\text{C}/\text{W}$
T_j	Junction Temperature	150	$^\circ\text{C}$
T_{stg}	Storage Temperature	-55~+150	$^\circ\text{C}$

SOT - 23



1. BASE
2. EMITTER
3. COLLECTOR

ELECTRICAL CHARACTERISTICS ($T_a=25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=0.1\text{mA}$, $I_E=0$				V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=1\text{mA}$, $I_B=0$				V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=0.1\text{mA}$, $I_C=0$				V
Collector cut-off current	I_{CBO}	$V_{CB}=40\text{V}$, $I_E=0$			0.1	μA
Collector cut-off current	I_{CEO}	$V_{CE}=20\text{V}$, $I_B=0$			0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=5\text{V}$, $I_C=0$			0.1	μA
DC current gain	$h_{FE(1)}$	$V_{CE}=1\text{V}$, $I_C=50\text{mA}$	200		350	
	$h_{FE(2)}$	$V_{CE}=1\text{V}$, $I_C=500\text{mA}$	40			
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=500\text{mA}$, $I_B=50\text{mA}$			0.6	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C=500\text{mA}$, $I_B=50\text{mA}$			1.2	V
Base-emitter voltage	V_{BE}	$V_{CB}=1\text{V}$, $I_C=10\text{mA}$			0.7	V
Transition frequency	f_T	$V_{CE}=6\text{V}$, $I_C=20\text{mA}$, $f=30\text{MHz}$	150			MHz
Collector output capacitance	C_{ob}	$V_{CB}=6\text{V}$, $I_E=0$, $f=1\text{MHz}$			8	pF



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